

1 Characteristics

Table 1. Absolute ratings (limiting values, per diode, at 25 °C unless otherwise specified)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			45	V	
I _{F(RMS)}	Forward rms current			10	A	
I _{F(AV)}	Average forward current	T _c = 140 °C, δ = 0.5 square wave	Per diode	7.5	A	
			Per device	15		
I _{FSM}	Surge non repetitive forward current		t _p = 10 ms sinusoidal	75	A	
P _{ARM}	Repetitive peak avalanche power		t _p = 10 μs, T _j = 125 °C	266	W	
T _{stg}	Storage temperature range			-65 to +175	°C	
T _j	Operating junction temperature range ⁽¹⁾			-40 to +150	°C	

1. $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Max. value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	4	°C/W
		Total	2.4	
$R_{th(c)}$	Coupling		0.7	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$	-		500	μA
		$T_j = 125\text{ °C}$		-	60	120	mA
$V_F^{(1)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 7.5\text{ A}$	-		0.52	V
		$T_j = 125\text{ °C}$		-	0.40	0.46	
		$T_j = 25\text{ °C}$	$I_F = 12\text{ A}$	-		0.60	
		$T_j = 125\text{ °C}$		-	0.49	0.57	
		$T_j = 25\text{ °C}$	$I_F = 15\text{ A}$	-		0.64	
		$T_j = 125\text{ °C}$		-	0.53	0.63	

1. $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 0.29 \times I_{F(AV)} + 0.023 \times I_{F(RMS)}^2$$

For more information, please refer to the following application notes related to the power losses :

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (per diode)

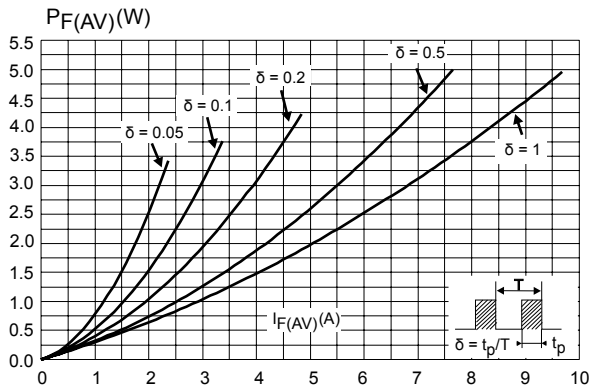


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

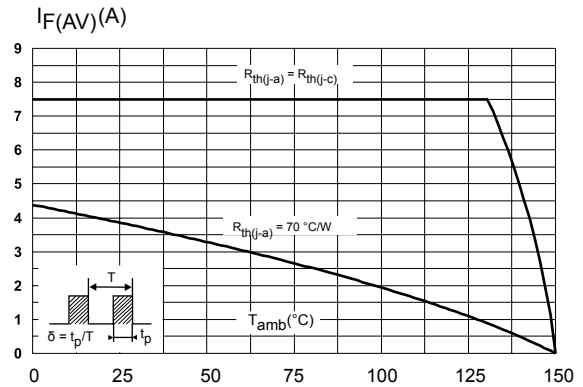


Figure 3. Normalized avalanche power derating versus pulse duration ($T_j = 125$ °C)

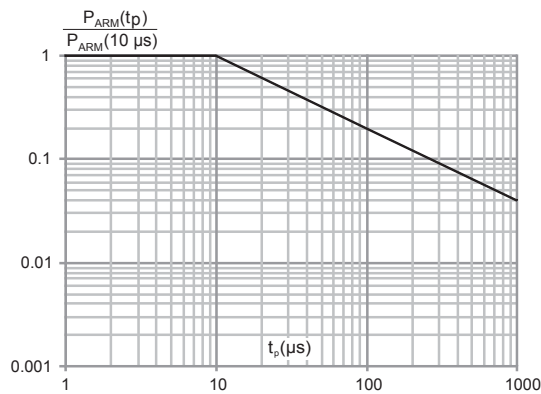


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

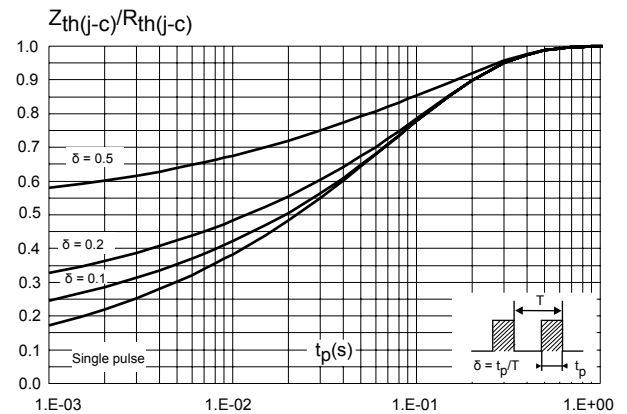


Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

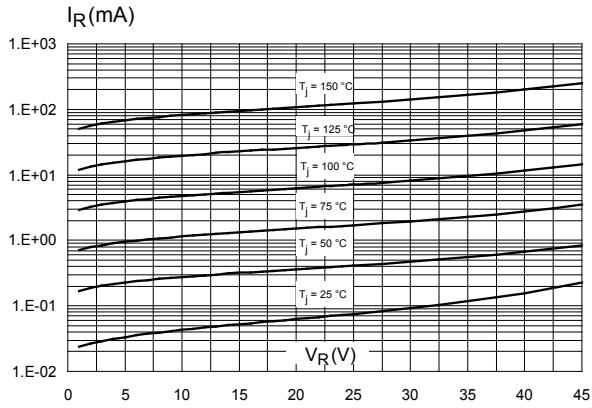


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

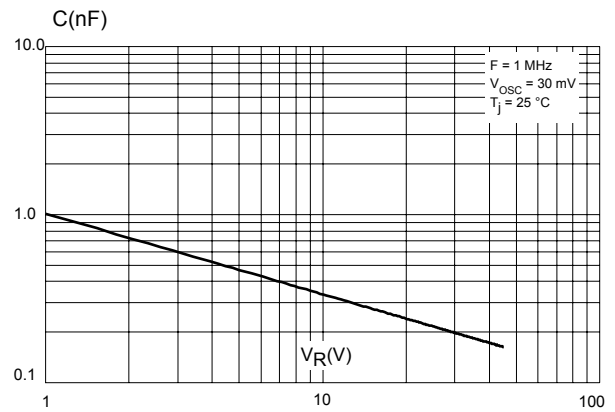


Figure 7. Forward voltage drop versus forward current (per diode)

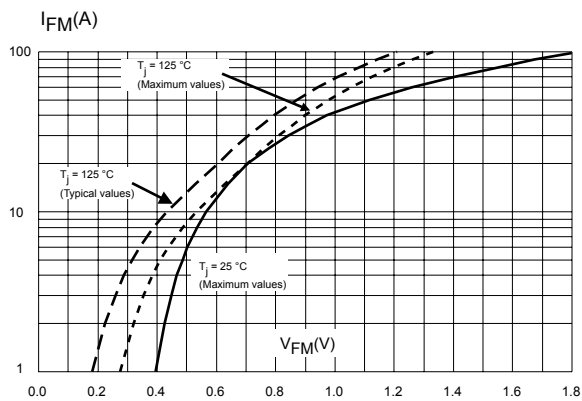
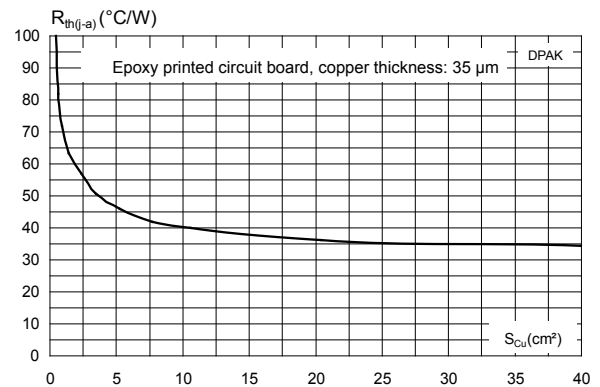


Figure 8. Thermal resistance junction to ambient versus copper surface under tab



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 DPAK package information

- Epoxy meets UL94, V0
- Lead-free packages

Figure 9. DPAK package outline

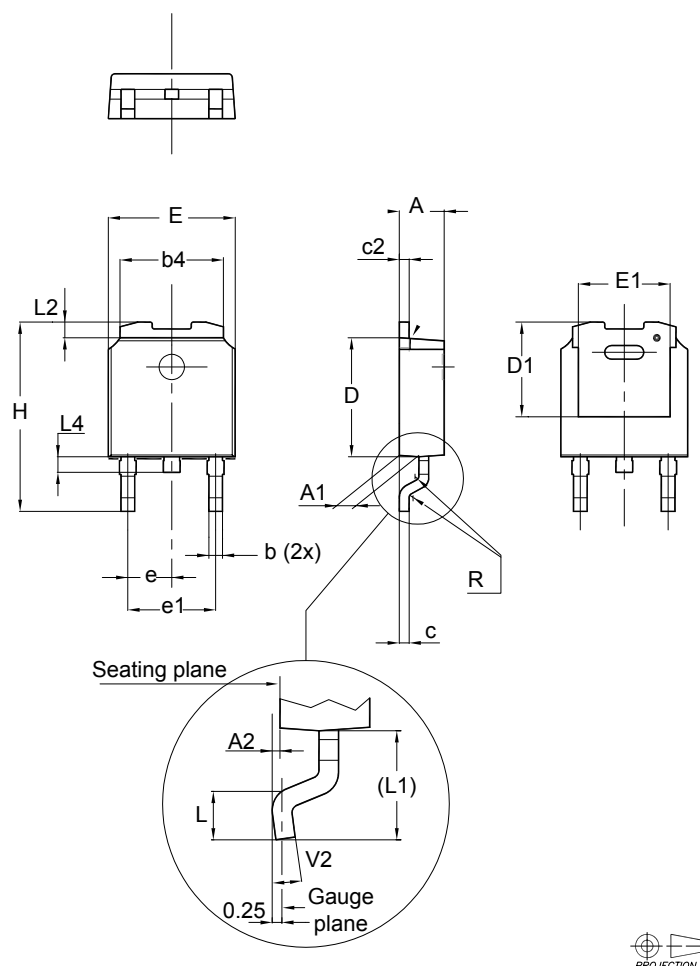
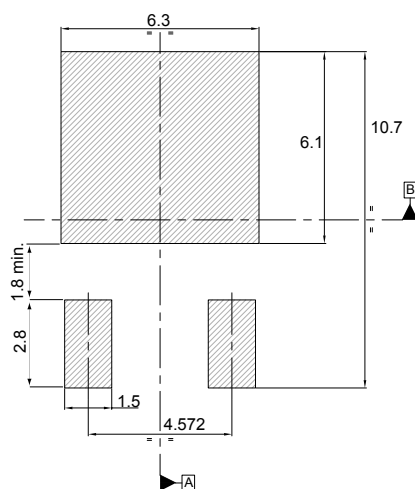


Table 4. DPAK mechanical data

Dim.	Dimensions					
	Millimeters			Inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	5.20		5.40	0.205		0.213
c	0.45		0.60	0.018		0.024
c2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
D1	4.95	5.10	5.25	0.195	0.201	0.207
E	6.40		6.60	0.252		0.260
E1	4.60	4.70	4.80	0.181	0.185	0.189
e	2.159	2.286	2.413	0.085	0.090	0.095
e1	4.445	4.572	4.699	0.175	0.180	0.185
H	9.35		10.10	0.368		0.398
L	1.00		1.50	0.039		0.059
(L1)	2.60	2.80	3.00	0.102	0.110	0.118
L2	0.65	0.80	0.95	0.026	0.031	0.037
L4	0.60		1.00	0.024		0.039
R		0.20			0.008	
V2	0°		8°	0°		8°

1. Inches dimensions given for reference only

Figure 10. DPAK recommended footprint (dimensions are in mm)


The device must be positioned within $\Phi 0.05 \text{ A B}$

3 Ordering Information

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS15L45CBY-TR	S15L45CY	DPAK	0.32 g	2500	Tape and reel

For a list of available options (e.g. memory size, package) and orderable part numbers or for further information on any aspect of this device, please go to www.st.com or contact the ST Sales Office nearest to you.

Note: *Qualified and characterized according to AEC Q101.*

Revision history

Table 6. Document revision history

Date	Version	Changes
10-Mar-2011	1	First issue.
07-Jul-2015	2	Updated Table 2. Format updated to current standard.
29-Nov-2018	3	Added Section Applications on cover page. Updated Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode) and Table 3. Static electrical characteristics (per diode) .

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